

Appendix A

Ted King Higman

Professional Preparation

Purdue University	W. Lafayette, IN	Electrical Engineering	BSEE 1981
Purdue University	W. Lafayette, IN	Electrical engineering	MSEE 1982
University of Illinois	Champaign, IL	Electrical Engineering	Ph. D. 1989

Appointments

Associate Professor, University of Minnesota, Twin-Cities, 1994-present

Assistant Professor, University of Minnesota, Twin Cities, 1989-1994

Research Assistant. University of Illinois at Urbana-Champaign, 1985-1989

LSI Process Engineer, Magnavox Corp., Ft. Wayne, IN, 1983-1984

Publications

[1.2V constant-gm rail-to-rail CMOS Op-Amp input stage with new overlapped transition regions technique for ECG amplifier](#)

Lee, B. & [Higman, T.](#), 2013, *Proceedings of the Annual International Conference of the IEEE Engineering in Medicine and Biology Society, EMBS*. Vol. 2013. p. 3451-3454 4 p. 6610284. (Proceedings of the Annual International Conference of the IEEE Engineering in Medicine and Biology Society, EMBS).

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[Real-time control of etching processes: Experimental results](#)

Berg, J., [Higman, T. K.](#) & Tannenbaum, A. R., 1997, In: [Proceedings of SPIE - The International Society for Optical](#)

[Silicon metal-oxide-semiconductor field-effect transistor with gate structures defined by scanned probe lithography](#)

Hagedorn, M. S., Litfin, D. D., Price, G. M., Gordon, A. E. & [Higman, T. K.](#), 1996, In: [Journal of Vacuum Science and Technology B: Microelectronics and Nanometer Structures](#). 14, 6, p. 4153-4156 4 p.

[Atomic force microscope-based lithography of titanium](#)

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